

PJQ5848

40V Dual N-Channel Enhancement Mode MOSFET

Voltage

Current 30 A

Features

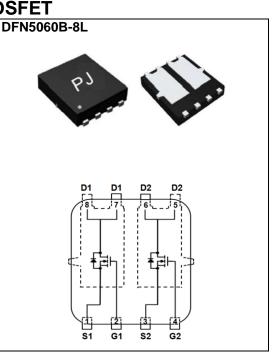
• $R_{DS(ON)}$, $V_{GS}@10V$, $I_D@12A<12m\Omega$

40 V

- R_{DS(ON)}, V_{GS}@4.5V, I_D@8A<16mΩ
- High switching speed
- Improved dv/dt capability
- Low reverse transfer capacitance
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

- Case : DFN5060B-8L Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight : 0.0035 ounces, 0.092 grams



Maximum Ratings and Thermal Characteristics ($T_A=25^{\circ}C$ unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V _{DS}	40	V	
Gate-Source Voltage		V _{GS}	<u>+</u> 20	V	
Continuous Drain Current (Note 4)	T _C =25°C		30		
	T _C =100°C	ID	19	А	
Pulsed Drain Current (Note 1)	T _C =25°C	I _{DM}	100		
Power Dissipation	T _C =25°C	D.	20	10/	
	T _C =100°C	Po	8	W	
Continuous Drain Current (Note 4)	T _A =25°C		8.6	Δ.	
	T _A =70°C	ID	7	A	
Power Dissipation	T _A =25°C	5	1.7		
	T _A =70°C	PD	1.1	W	
Single Pulse Avalanche Energy (Note 6)		E _{AS}	62	mJ	
Operating Junction and Storage Temperature Range		T _J ,T _{STG}	-55~150	°C	
Typical Thermal Resistance (Note 4,5)	Junction to Case	R _{θJC}	6.3	°0.001	
	Junction to Ambient	R _{θJA}	73.5	°C/W	

November 15,2017-REV.00



Electrical Characteristics ($T_A=25^{\circ}C$ unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static	0111202				in ou	
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250uA	40	-	-	
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250uA	1	1.7	2.5	V
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =10V, I _D =12A V _{GS} =4.5V, I _D =8A	-	10	12	mΩ
Drain-Source On-State Resistance	R _{DS(on)}		-	13	16	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =40V, V _{GS} =0V	-	-	1	uA
Gate-Source Leakage Current	I _{GSS}	V _{GS} = <u>+</u> 20V, V _{DS} =0V	-	-	<u>+</u> 100	nA
Dynamic (Note 7)		·				
Total Gate Charge	Qg	V _{DS} =20V, I _D =10A, V _{GS} =4.5V ^(Note 2,3)	-	10	-	nC
Gate-Source Charge	Q _{gs}		-	3.5	-	
Gate-Drain Charge	Q _{gd}		-	3.6	-	
Input Capacitance	Ciss	V _{DS} =20V, V _{GS} =0V, f=1MHZ	-	1040	-	pF
Output Capacitance	Coss		-	117	-	
Reverse Transfer Capacitance	Crss		-	84	-	
Turn-On Delay Time	td _(on)	$V_{DS}=20V, I_{D}=1A,$ $V_{GS}=10V, R_{G}=6\Omega$ (Note 2,3)	-	9.4	-	ns
Turn-On Rise Time	tr		-	19	-	
Turn-Off Delay Time	td _(off)		-	66	-	
Turn-Off Fall Time	t _f		-	67	-	
Drain-Source Diode						
Maximum Continuous Drain-Source Diode Forward Current	I _S		-	-	30	A
Diode Forward Voltage	V _{SD}	I _S =1A, V _{GS} =0V	-	0.7	1	V

NOTES :

- 1. Pulse width
- 2. Essentially independent of operating temperature typical characteristics.
- Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150°C. Ratings are based on low frequency and duty cycles to keep initial T_J =25°C.
- 4. The maximum current rating is package limited.
- 5. $R_{\Theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. The test condition is L=0.1mH, I_{AS} =35A, V_{DD} =25V, V_{GS} =10V, Starting T_J =25°C.
- 7. Guaranteed by design, not subject to production testing.

November 15,2017-REV.00

100 20 V_{GS}=10V,8V,6V,5V V_{DS}=5V V_{GS}=4.5V I_{DS}-Drain-to-S ource Current(A) IDS-Drain-to-S ource Current(A) 75 V_{GS}=4V 15 V_{GS}=3.5V 50 10 V_{GS}=3V T_J=125℃ TJ=25℃ 25 5 V_{GS}=2.5V 0 0 0 1 2 3 4 5 0 1 5 2 3 4 V_{DS}- Drain-to-Source Voltage(V) V_{GS}-Gate-to-Source Voltage(V) **Fig.1 Output Characteristics Fig.2 Transfer Characteristics** 22 2.5 R_{DS}(on)- On-Resistance (Normalized) $R_{DS}(on)$ - On-Resistance(m Ω) 18 2.0 V_{GS} =10V, I_{D} =12A V_{GS}= 4.5V 1.5 14 V_{GS}=4.5V, I_D=8A $V_{GS} = 10V$ 1.0 10 0.5 6 0 25 50 75 100 125 150 175 0 5 10 15 20 Temperature (°C) I_{DS}-Drain-to-Source Current(A) Fig.3 On-Resistance vs. Drain Current Fig.4 On-Resistance vs. Junction temperature 10 50 I_D=6A I_{sD}-Source to Drain Current(A) $R_{DS}(on)$ - On-Resistance(m Ω) 40 1 30 T_i=125℃ 20 Tj=25℃ T_i=125°C 0.1 T_i=25℃ 10 0 0.01 2 4 6 8 10 0 0.3 0.6 0.9 1.2 V_{GS}-Gate-to-Source Voltage(V) V_{SD}-Source-to-Drain Voltage(V) Fig.5 On-Resistance Variation with V_{GS} Fig.6 Source-Drain Diode Forward Voltage

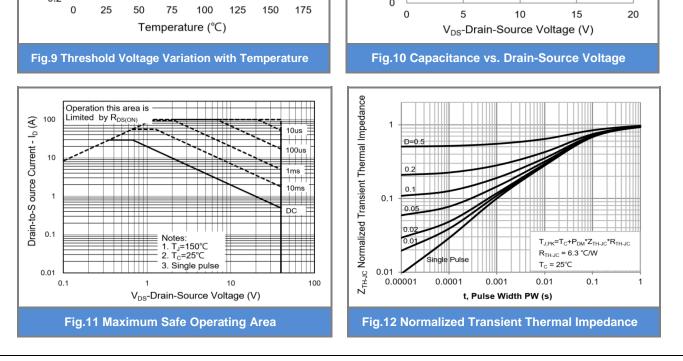
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TYPICAL CHARACTERISTIC CURVES

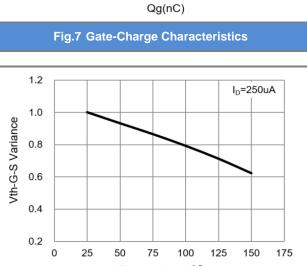








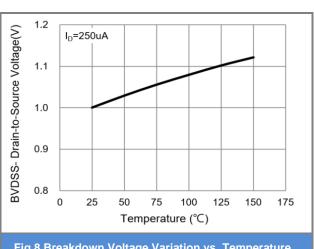
1.2 I_D=250uA 1.0 Vth-G-S Variance 0.8 0.6 0.4 0.2



10

15

20



TYPICAL CHARACTERISTIC CURVES



10

8

6

4

2

0

0

5

V_{GS}-Gate-to-Source Voltage(V)

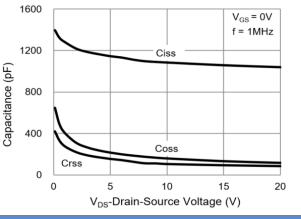
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V_{DS}= 20V

I_D=10A



Fig.8 Breakdown Voltage Variation vs. Temperature



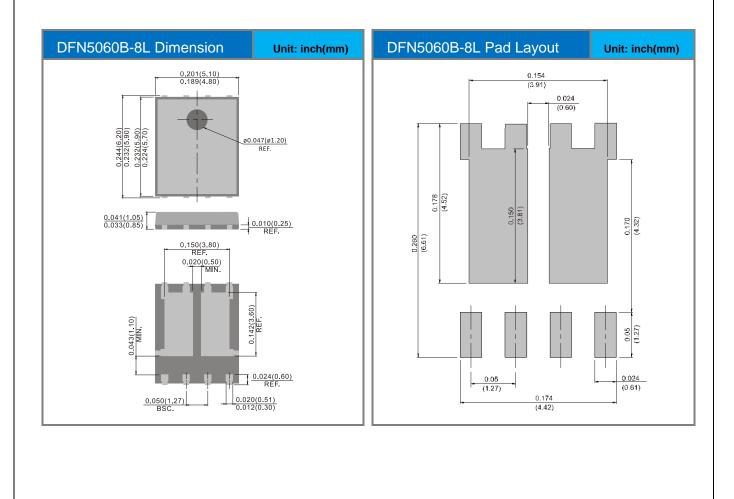


PJQ5848

Part No Packing Code Version

Part No Packing Code	Package Type	Packing Type	Marking	Version
PJQ5848_R2_00001	DFN5060B-8L	3000pcs / 13" reel	Q5848	Halogen free

Packaging Information & Mounting Pad Layout





PJQ5848

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